

ONS00502
10/623,390REMARKS

Claims 1-9, 11-15, and 17-20 are in the application. Claims 10 and 16 have been cancelled. The allowable subject matter of claims 5-8, 13, and 14 is noted.

By this amendment, claims 1-9, 11-13, 15, and 17-20 have been amended to more particularly set out applicant's invention. Paragraphs [0033]-[0046] support the claim amendments.

Claims 1-4, 9-12, 15, 19 and 20 were rejected under 35 U.S.C. §103(a) as unpatentable over Yuan, et al., USP No. 5,610,085 ("Yuan") in further view of Rinne, et al., USP No. 6,628,532 ("Rinne"). This rejection is respectively traversed in view of the amendments made herein and the remarks presented hereinafter.

Applicant first wishes to address the rejection of independent claim 15. Applicant has amended claim 15 to include the subject matter of objected to claim 16, and in view of the Examiner's comments in the present Office Action, applicant respectfully believes that claim 15 is now allowable as are claims 17 and 18, which depend therefrom.

Applicant has further amended independent claim 19 similar to claim 15, and respectfully submits that claim 19 is now allowable. Claim 20 depends from claim 19 and is believed allowable for at least the same reasons as claim 19.

Claim 1 has been amended and now calls for a dc/dc converter comprising an inductor coupled to one of a positive output terminal and a positive input terminal. A first depletion mode compound semiconductor switching FET is connected to the inductor and configured to control current flow in the inductor. A control circuit is coupled to a

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gate of the first depletion mode compound semiconductor switching FET for switching the first depletion mode compound semiconductor switching FET between an on state and an off state. A capacitor is coupled to the positive output terminal and a negative terminal.

Applicant agrees with the statement of the Examiner in the present Office Action that Yuan fails to show or suggest a first depletion mode device as is called for in claim 1. However, the applicant respectfully submits that Rinne makes up for the deficiencies of Yuan for at least the following reason. Claim 1 calls for a first depletion mode compound semiconductor switching device configured to control current flow in the inductor. However, in Rinne, the device referred to by the Examiner is Rinne's control circuit or gate driver device (see Rinne col. 2, lines 28-39), which is not a switching device connected to the inductor and configured as called for in claim 1.

More specifically, the switching device in Rinne (e.g., device 80) device is a MOSFET synchronous rectifier or a rectifying diode (see Rinne col. 54-56). Moreover, Rinne does not expressly state or suggest any where that switching device 80 is a depletion mode compound semiconductor switching FET as is called for in claim 1. Thus, the combination of Yuan and Rinne cannot make claim 1 obvious.

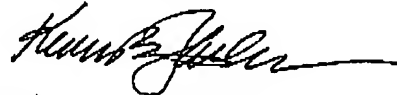
Rejected claims 2-4, 9, and 11-12 depend from claim 1 and are believed allowable for at least the same reasons as claim 1.

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In view of all of the above, it is believed that the claims are allowable, and the case is in condition for allowance, which action is earnestly solicited.

Respectfully submitted,

Peyman Hadizad



Kevin B. Jackson
Attorney for Applicant
Reg. No. 38,502
Tel. (602) 244-4885

ON Semiconductor
Intellectual Property Dept.
P.O. Box 62890; M/D A700
Phoenix, AZ 85082-2890

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